01) 500 500

MgO: 0.1 to 3 moles,

MnO: 0.05 to 1.0 mole

 Y_2O_3 : 1 mole or less,

BaO+CaO: 2 to 12 moles, and

 SiO_2 :/2 to 12 moles.

3. (Amended) The EL device according to claim 1 or 2, wherein BaO, CaO and SiO₂ are present in at least one of the first and second insulator layers in the form of (Ba_xCa₁. $_{x}O)_{y}\cdot SiO_{2}$ where $0.3 \le x \le 0.7$ and $0.95 \le y \le 1.05$ and in an amount of 1 to 10% by weight with respect to the sum of the weights of BaTiO₃, MgO, MnO and Y₂O₃.

4. (Twice Amended) The EL device according to claim 2, wherein said first electrode comprises one or two or more of Ni, Ag, Au, Pd, Pt, Cu, W, Fe, and Co or any one of Ag-Pd, Ni-Mn, Ni-Cr, Ni-Co and Ni-Al alloys.

5. (Twice Amended) The EL device according to claim 3, wherein said first electrode comprises one or two or more of Ni, Ag, Au, Pd, Pt, Cu, W, Fe, and Co or any one of Ag-Pd, Ni-Mn, Ni-Cr, Ni-Co and Ni-Al alloys.

Please add the following new claims:

6. (New) The EL device of Claim 1, wherein the light emitting layer comprises at least one material selected from the group consisting of ZnS, Mn/CdSSe, ZnS:TbOF, ZnS:Tb, SrS:Ce, (SrS:Ce/ZnS)_n, CaGa₂S₄:Ce, and SrS:Ce/ZnS:Mn.

- 7. (New) The EL device of Claim 1, wherein the light emitting layer has a thickness of 100 to 1000 nm.
- 8. (New) The EL device of Claim 1, wherein the second electrode comprises at least one material selected from the group consisting of tin-doped indium oxide, zinc-doped indium oxide, indium oxide, tin oxide, and zinc oxide.

9. (New) The EL device of Claim 1, wherein the amount of MgO relative to 100 moles of barium titanate is 0.5 to 1.5 moles.

10. (New) The EL device of Claim 1, wherein the amount of MnO relative to 100 moles of barium titanate is 0.2 to 0.4 moles.

- 11. (New) The EL device of Claim 1, wherein the ratio (BaO + CaO)/SiO₂ is in the range of 0.9 to 1.1.
- 12. (New) The EL device of Claim 1, wherein the amount of yttrium oxide is in the range of 0.1 to 1 moles relative to 100 moles of barium titanate.
- 13. (New) The EL device of Claim 1, wherein the first insulator layer has an average crystal grain diameter of 0.2 to 0.7 μm .
- 14. (New) The EL device of Claim 1, wherein the first electrode comprises a material selected from the group consisting of Ag, Pd, and Ag-Pd alloys.
- 15. (New) The EL device of Claim 1, wherein the substrate comprises Al₂O₃ and optionally one or more oxides selected from the group consisting of SiO₂, MgO, and CaO.

IN THE ABSTRACT

Please amend the abstract to read as follows: